



**TET ESTEL AS**  
ESTONIA

**May**  
**2016**

**Series**  
**TFI233-400**

**High Frequency Inverter grade**  
**Capsule Thyristor**  
**Type TFI233-400**

Low turn-off time  
Low reverse recovery charge  
Distributed amplified gate for high di/dt

Maximum mean on-state current					$I_{TAV}$	<b>400 A</b>		
Maximum repetitive peak off-state and reverse voltage					$U_{DRM}$	<b>800 ÷ 1500 V</b>		
Turn-off time					$U_{RRM}$			
					$t_q$	<b>16; 20; 25; 32 μs</b>		
$U_{DRM}, U_{RRM}, V$	800	900	1000	1100	1200	1300	1400	1500
Voltage code	8	9	10	11	12	13	14	15
$T_{vj}, °C$	- 60 ÷ 125							

**MAXIMUM ALLOWABLE RATINGS**

Symbols and parameters		Units	TFI233-400	Conditions
$I_{TAV}$	Mean on-state current	A	400 635	$T_c=88 °C$ , $T_c=55 °C$ , 180° half-sine wave, 50 Hz
$I_{TRMS}$	RMS on-state current	A	628	$T_c=88 °C$
$I_{TSM}$	Surge on-state current	kA	7,0 7,7	$T_{vj}=125 °C$ $T_{vj}=25 °C$ tp=10 ms $U_R=0$
$I^2t$	Limiting load integral	kA <sup>2</sup> s	245 296	$T_{vj}=125 °C$ $T_{vj}=25 °C$
$U_{DRM}, U_{RRM}$	Repetitive peak off-state and reverse voltage	V	800 ÷ 1500	$T_j \min \leq T_{vj} \leq T_{jM}$ 180° half-sine wave, 50 Hz Gate open
$U_{DSM}, U_{RSM}$	Non-repetitive peak off-state and reverse voltage	V	880 ÷ 1600	$T_j \min \leq T_{vj} \leq T_{jM}$ 180° half-sine wave tp=10 ms, Single pulse Gate open
(diT/dt) crit	Critical rate of rise of on-state current : non - repetitive repetitive	A/μs	1600 800	$T_{vj}=125 °C$ ; $U_D=0,67 U_{DRM}$ , Gate pulse : 10V, 5 Ω, 1 μs rise time, 10 μs
$U_{RGM}$	Peak reverse gate voltage	V	5	$T_j \min \leq T_{vj} \leq T_{jM}$
$T_{stg}$	Storage temperature	°C	-60 ÷ 80	
$T_{vj}$	Junction temperature	°C	-60 ÷ 125	

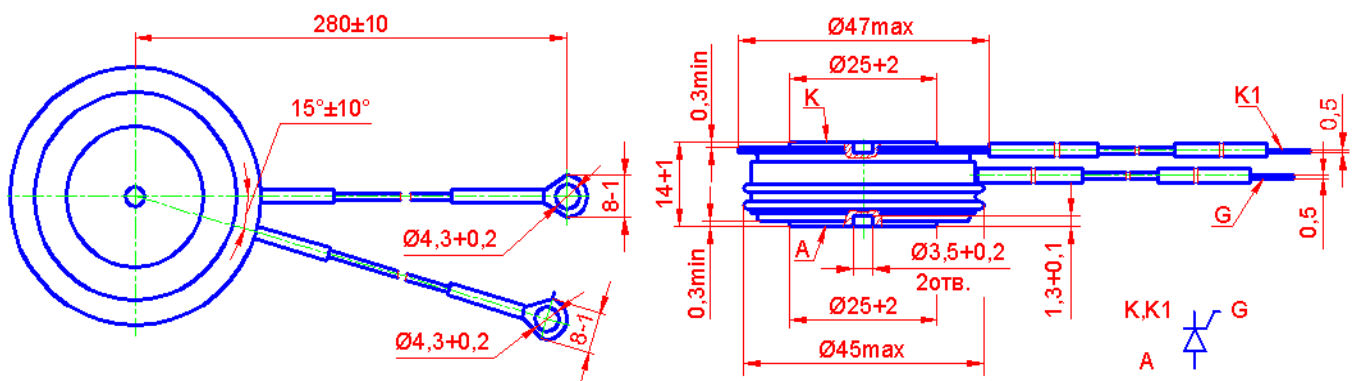
**CHARACTERISTICS**

$U_{TM}$	Peak on-state voltage	V	2,6	$T_{vj}=25 °C$ , $I_{TM}=3,14 I_{TAV}$
$U_{T(TO)}$	Threshold voltage	V	1,4	$T_{vj}=125 °C$
$R_T$	On-state slope resistance	mΩ	0,85	$1,57 I_{TAV} < I_T < 4,71 I_{TAV}$
$I_{DRM}$ $I_{RRM}$	Repetitive peak off-state and reverse current	mA	50 50	$T_{vj}=125 °C$ , $U_D = U_{DRM}$ $U_R = U_{RRM}$

CHARACTERISTICS				
Symbols and parameters		Units	TFI233-400	Conditions
$I_L$	Latching current	A	5	$T_{vj}=25^{\circ}\text{C}, U_D=12\text{V}$ Gate pulse : 10V, 5 $\mu\text{s}$ , 1 $\mu\text{s}$ rise time, 10 $\mu\text{s}$
$I_H$	Holding current	A	0,5	$T_{vj}=25^{\circ}\text{C}, U_D=12\text{V}$ , Gate open
$U_{GT}$	Gate trigger direct voltage	V	2,5 5,0	$T_{vj}=25^{\circ}\text{C}$ , $T_{vj}=-60^{\circ}\text{C}$ <span style="float:right"><math>U_D=12\text{V}</math></span>
$I_{GT}$	Gate trigger direct current	A	0,3 0,85	$T_{vj}=25^{\circ}\text{C}$ , $T_{vj}=-60^{\circ}\text{C}$
$U_{GD}$	Gate non-trigger direct voltage	V	0,25	$T_{vj}=125^{\circ}\text{C}$ , $U_D = 0,67 U_{DRM}$ Direct gate current
$I_{GD}$	Gate non-trigger direct current	mA	10	
$t_{gd}$	Delay time	$\mu\text{s}$	1,6	$T_{vj}=25^{\circ}\text{C}, U_D=500\text{V}$ $I_{TM} = 400 \text{ A}$
$t_{gt}$	Turn-on time	$\mu\text{s}$	2,5	Gate pulse : 10V, 5 $\mu\text{s}$ , 1 $\mu\text{s}$ rise time, 10 $\mu\text{s}$
$t_q$	Turn-off time	$\mu\text{s}$	16÷32 20÷40	$T_{vj}=125^{\circ}\text{C}$ , $I_{TM} = 400 \text{ A}$ $di_R/dt = 10 \text{ A}/\mu\text{s}$ , $U_R=100\text{V}$ $U_D = 0,67 U_{DRM}$ $du_D/dt=50 \text{ V}/\mu\text{s}$ $du_D/dt=200 \text{ V}/\mu\text{s}$
$Q_{rr}$	Recovered charge	$\mu\text{C}$	170	
$t_{rr}$	Reverse recovery time	$\mu\text{s}$	3,2	$T_{vj}=125^{\circ}\text{C}$ , $I_{TM} = 500 \text{ A}$
$I_{rrm}$	Peak reverse recovery current	A	110	$di_R/dt = 50 \text{ A}/\mu\text{s}$ , $U_R=100\text{V}$
$(du_D/dt)_{crit}$	Critical rate of rise of off-state voltage	$\text{V}/\mu\text{s}$	500 1000	$T_{vj}=125^{\circ}\text{C}$ , $U_D = 0,67 U_{DRM}$ Gate open
$R_{thjc}$	Thermal resistance junction to case	$^{\circ}\text{C}/\text{W}$	0,04	Direct current, double side cooled

ORDERING								
	<b>TFI</b>	<b>233</b>	<b>400</b>	<b>14</b>	<b>7</b>	<b>6</b>	<b>3</b>	
	<b>1</b>	<b>2</b>	<b>3</b>	<b>4</b>	<b>5</b>	<b>6</b>	<b>7</b>	

- Fast thyristor with interdigitated gate structure.
- Design version.
- Mean on-state current, A.
- Voltage code (14=1400 V).
- Critical rate of rise of off-state voltage ( $6 \geq 500 \text{ V}/\mu\text{s}$ ,  $7 \geq 1000 \text{ V}/\mu\text{s}$ ).
- Group of turn-off time ( $du_D/dt=50 \text{ V}/\mu\text{s}$ ,  $4 \leq 32 \mu\text{s}$ ,  $5 \leq 25 \mu\text{s}$ ,  $6 \leq 20 \mu\text{s}$ ,  $7 \leq 16 \mu\text{s}$ ).
- Group of turn-on time ( $3 \leq 2,5 \mu\text{s}$ ).



Mounting force : 9÷12 kN  
Weight : 120 grams